

Claims

1. A sputtering target comprising:

a material containing silicon carbide and silicon

5 wherein a volume ratio of the silicon carbide ranges from about 50% to about 70% when a volume ratio of silicon carbide equals the entire volume of silicon carbide/ (the entire volume of silicon carbide + the entire volume of silicon) \times 100.

10 2. The sputtering target as claimed in claim 1 wherein the volume ratio of the silicon carbide is about 55% to about 65%.

3. The sputtering target as claimed in claim 1 or 2 wherein the material containing silicon carbide and silicon is prepared
15 by a reaction sintering method.

4. The sputtering target as claimed in any one of claims 1, 2 and 3 wherein a weight ratio of impurities contained in the silicon is about 0.01% or less.

20